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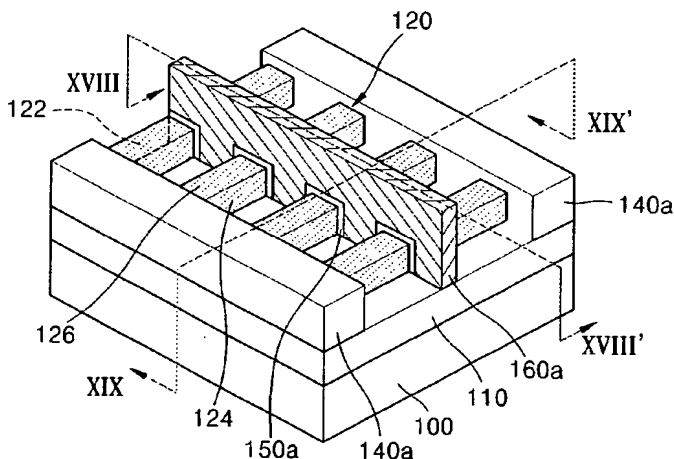
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(54) Title: SEMICONDUCTOR DEVICE HAVING MULTI-GATE STRUCTURE AND METHOD OF MANUFACTURING THE
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(57) Abstract: Provided are a semiconductor device
having a mesa-type active region including a plurality
of slabs and a method of manufacturing the semicon-
ductor device. The semiconductor device includes a
first active region and a second active region. The first
active region is formed in a line-and-space pattern on
a substrate and includes the slabs, each slab having a
first surface, a second surface facing a direction op-
posite to the first side, and a top surface. The first
active region and the second active region are composed
of identical or different materials. The second active
region contacts at least one end of each of the slabs
on the substrate to connect the slabs to one another.
The method includes forming a first active region in
a line-and-space pattern on the substrate and forming
the second active region.